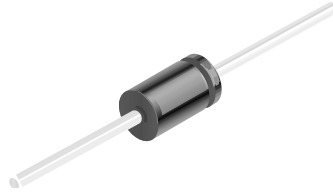


BAV19 / 20 / 21



DO-35

Color Band Denotes Cathode

Small Signal Diode

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{RRM}	Maximum Repetitive Reverse Voltage	BAV19	120
		BAV20	200
		BAV21	250
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	1.0	A
		4.0	A
T_{stg}	Storage Temperature Range	-65 to +200	$^\circ\text{C}$
T_J	Operating Junction Temperature	175	$^\circ\text{C}$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 200 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Symbol	Parameter	Value	Units
P_D	Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	$^\circ\text{C}/\text{W}$

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
V_R	Breakdown Voltage	BAV19 $I_R = 100 \mu\text{A}$	120		V
		BAV20 $I_R = 100 \mu\text{A}$	200		V
		BAV21 $I_R = 100 \mu\text{A}$	250		V
V_F	Forward Voltage	$I_F = 100 \text{ mA}$		1.0	V
		$I_F = 200 \text{ mA}$		1.25	V
I_R	Reverse Current	$V_R = 100 \text{ V}$		100	nA
		BAV19 $V_R = 100 \text{ V}, T_A = 150^\circ\text{C}$		100	μA
		$V_R = 150 \text{ V}$		100	nA
		BAV20 $V_R = 150 \text{ V}, T_A = 150^\circ\text{C}$		100	μA
		$V_R = 200 \text{ V}$		100	nA
BAV21 $V_R = 200 \text{ V}, T_A = 150^\circ\text{C}$		100	μA		
C_T	Total Capacitance	$V_R = 0, f = 1.0 \text{ MHz}$		5.0	pF
t_{rr}	Reverse Recovery Time	$I_F = I_R = 30 \text{ mA}, I_{RR} = 3.0 \text{ mA}, R_L = 100\Omega$		50	ns

Typical Characteristics

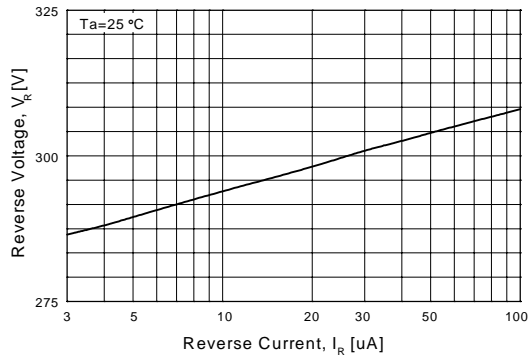


Figure 1. Reverse Voltage vs Reverse Current
BV - 1.0 to 100uA

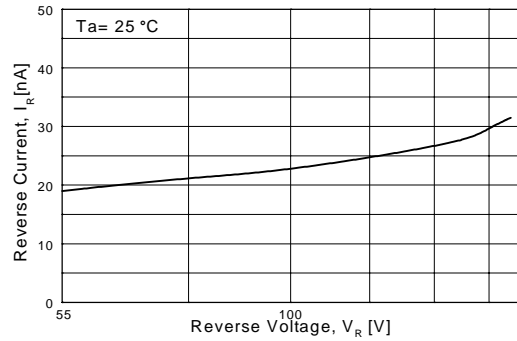


Figure 2. Reverse Current vs Reverse Voltage
IR - 55 to 205 V
GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

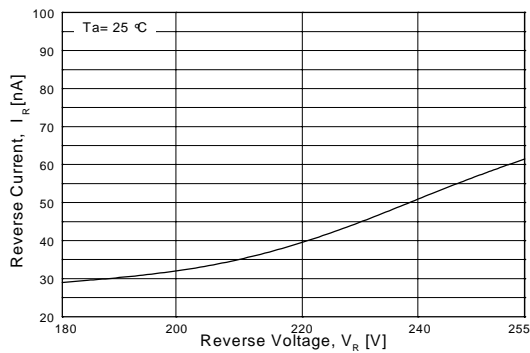


Figure 3. Reverse Current vs Reverse Voltage
IR - 180 to 225 V
GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

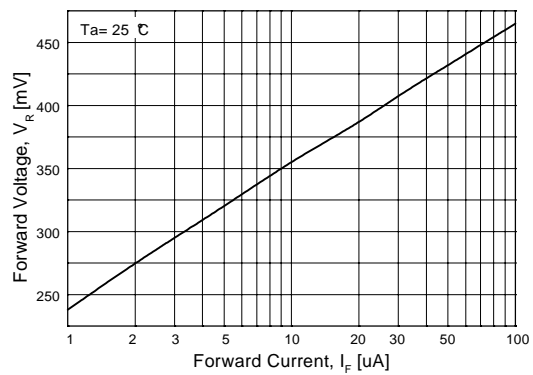


Figure 4. Forward Voltage vs Forward Current
VF - 1.0 to 100uA

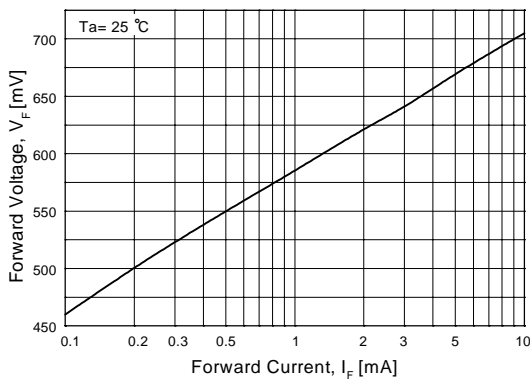


Figure 5. Forward Voltage vs Forward Current
VF - 0.1 to 10mA

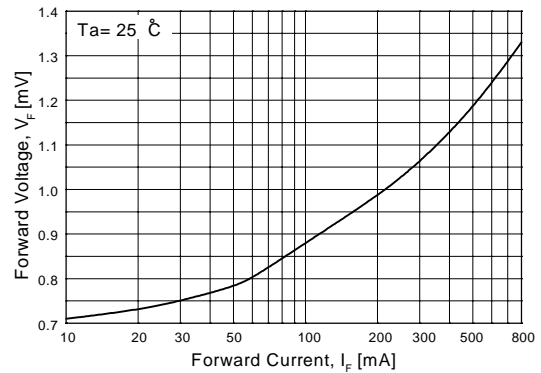


Figure 6. Forward Voltage vs Forward Current
VF - 10 to 800mA

Typical Characteristics (continued)

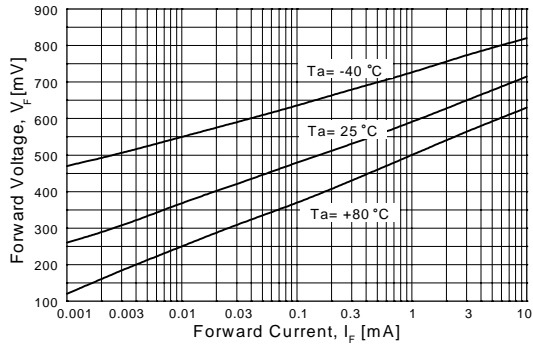


Figure 7. Forward Voltage vs Ambient Temperature
VF - 1.0 uA - 10 mA (-40 to +80 Deg C)

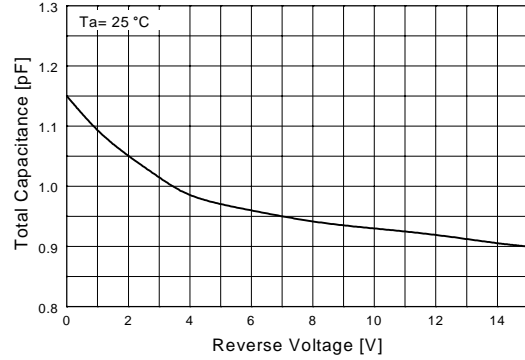


Figure 8. Total Capacitance

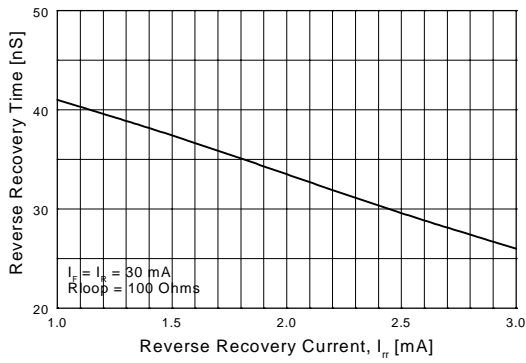


Figure 9. Reverse Recovery Time vs Reverse Recovery Current

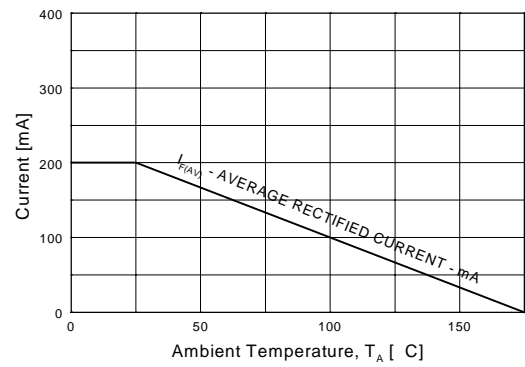


Figure 10. Average Rectified Current ($I_{F(AV)}$) versus Ambient Temperature (T_A)

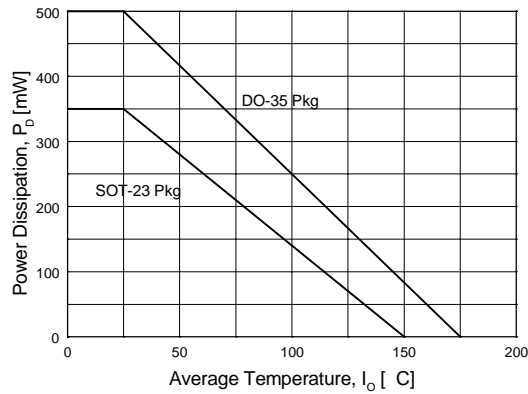


Figure 11. Power Derating Curve

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